

MJ P-Channel Enhancement Mode Power MOSFET

Description

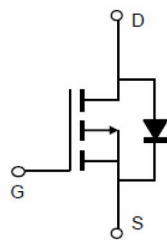
The MJ30P28Q uses advanced trench technology to provide excellent $R_{DS(ON)}$, This device is suitable for use as a load switch or power management.

General Features

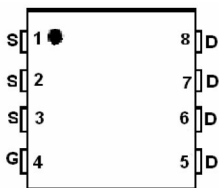
- ◆ $V_{DS}=-30V, I_D=-28A$
 $R_{DS(ON)}<9m\Omega @ V_{GS}=-10V$
 $R_{DS(ON)}<17m\Omega @ V_{GS}=-4.5V$
- ◆ High Power and current handing capability
- ◆ Lead free product is acquired
- ◆ Surface mount package

Application

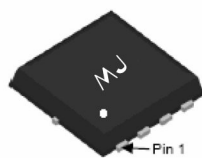
- ◆ Power management
- ◆ Load switch



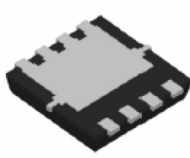
Schematic diagram



Pin Assignment



Top View



Bottom View

100% UIS TESTED!

Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|----------------|----------|----------------|-----------|------------|----------|
| MJ30P28Q | MJ30P28Q | DFN3.3X3.3-8L | | | |

Absolute Maximum Ratings ($T_c=25\text{ }^{\circ}\text{C}$ unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|--|----------------|------------|--------------------|
| Drain-Source Voltage | V_{DS} | -30 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Drain Current-Continuous | I_D | -28 | A |
| Drain Current-Pulsed ^(Note 1) | I_{DM} | -80 | A |
| Maximum Power Dissipation | P_D | 40 | W |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 To 150 | $^{\circ}\text{C}$ |

Thermal Characteristic

| | | | |
|--|-----------------|------|----------------------|
| Thermal Resistance, Junction-to-Case ^(Note 2) | $R_{\theta JA}$ | 3.13 | $^{\circ}\text{C/W}$ |
|--|-----------------|------|----------------------|

Electrical Characteristics (T_A =25℃unless otherwise noted)

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|---|---------------------|--|------|------|------|------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V I _D =-250μA | -30 | - | - | V |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =-30V,V _{GS} =0V | - | - | -1 | μA |
| Gate-Body Leakage Current | I _{GSS} | V _{DS} =±20V,V _{GS} =0V | - | - | ±100 | nA |
| On Characteristics ^(Note 3) | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} =V _{GS} ,I _D =-250μA | -1.0 | -1.7 | -2.5 | V |
| Drain-Source On-State Resistance | R _{DS(ON)} | V _{GS} =-10V, I _D =-20A | - | 6.7 | 9 | mΩ |
| | | V _{GS} =-4.5V, I _D =-20A | - | 9.5 | 17 | mΩ |
| Forward Transconductance | g _{FS} | V _{DS} =-10V,I _D =-20A | - | 25 | - | S |
| Dynamic Characteristics ^(Note 4) | | | | | | |
| Input Capacitance | C _{iss} | V _{DS} =-15V,V _{GS} =0V, F=1.0MHz | - | 2060 | - | PF |
| Output Capacitance | C _{OSS} | | - | 370 | - | PF |
| Reverse Transfer Capacitance | C _{rss} | | - | 295 | - | PF |
| Switching Characteristics ^(Note 4) | | | | | | |
| Turn-on Delay Time | t _{d(on)} | V _{DD} =-15V, I _D =-20A, V _{GS} =-10V,R _{GEN} =3Ω | - | 11 | - | nS |
| Turn-on Rise Time | t _r | | - | 9.4 | - | nS |
| Turn-Off Delay Time | t _{d(off)} | | - | 24 | - | nS |
| Turn-Off Fall Time | t _f | | - | 12 | - | nS |
| Total Gate Charge | Q _g | V _{DS} =-15V,I _D =-20A, V _{GS} =-10V | - | 30 | - | nC |
| Gate-Source Charge | Q _{gs} | | - | 4.5 | - | nC |
| Gate-Drain Charge | Q _{gd} | | - | 9.5 | - | nC |
| Drain-Source Diode Characteristics | | | | | | |
| Diode Forward Voltage ^(Note 3) | V _{SD} | V _{GS} =0V,I _S =-28A | - | | -1.2 | V |

Notes:

- ① Repetitive Rating: Pulse width limited by maximum junction temperature.
- ② Surface Mounted on FR4 Board, t ≤ 10 sec.
- ③ Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
- ④ Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

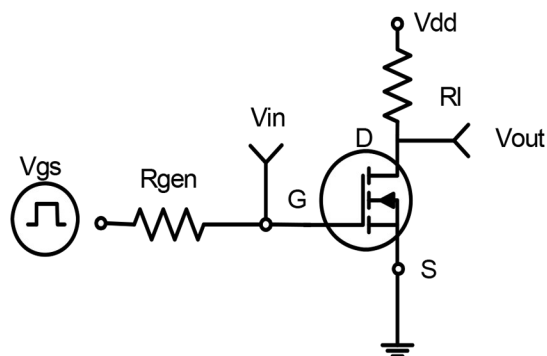


Figure 1 Switching Test Circuit

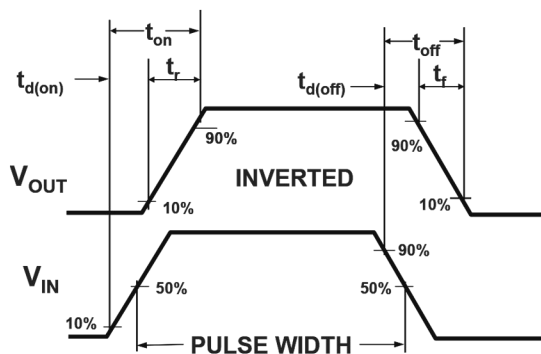


Figure 2 Switching Waveforms

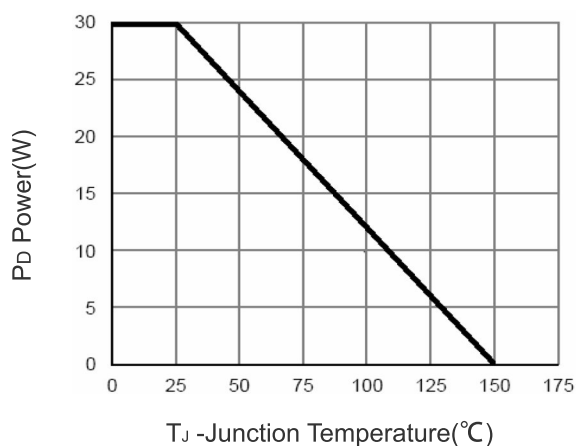


Figure 3 Power Dissipation

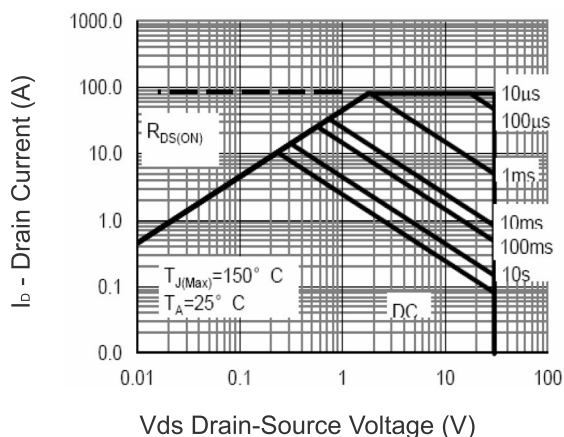


Figure 4 Safe Operation Area

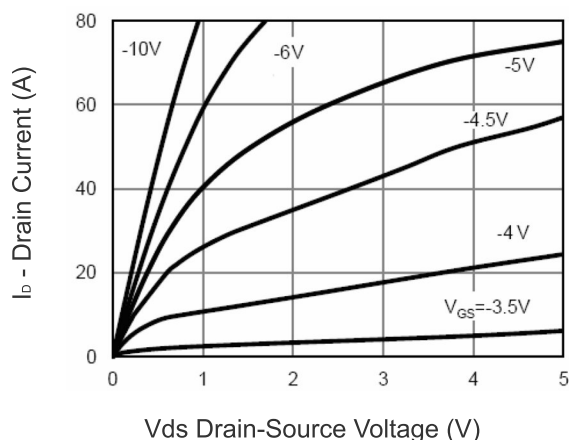


Figure 5 Output Characteristics

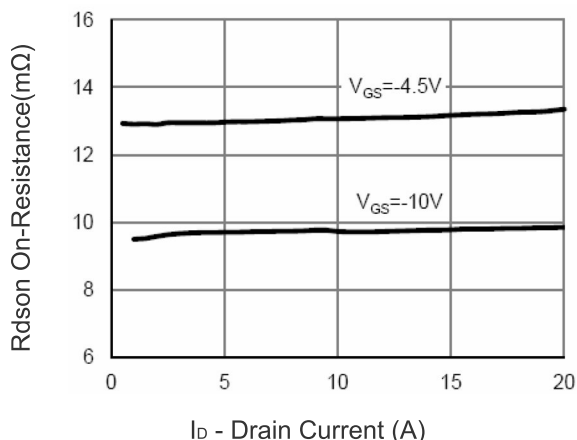


Figure 6 Drain-Source On-Resistance

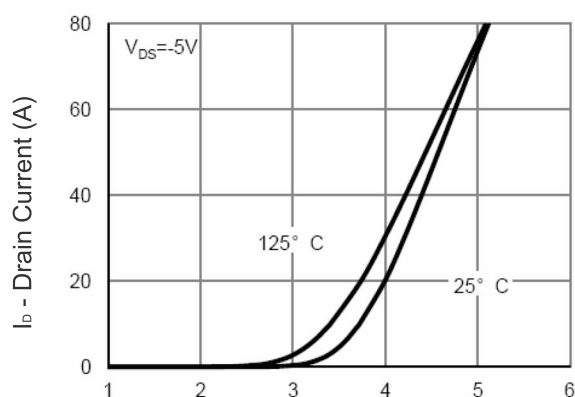

V_{GS} Gate-Source Voltage (V)

Figure 7 Transfer Characteristics

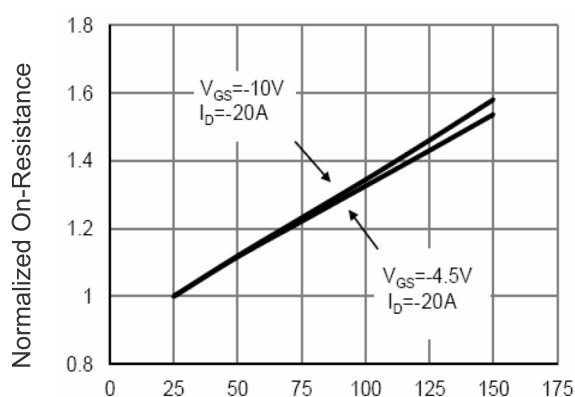

T_J -Junction Temperature(°C)

Figure 8 Drain-Source On-Resistance

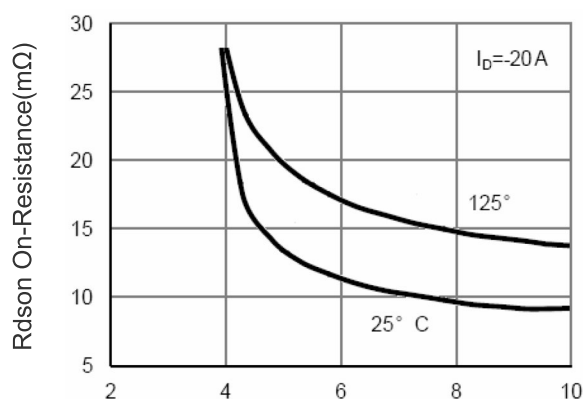

V_{GS} Gate-Source Voltage (V)

Figure 9 Rdson vs Vgs

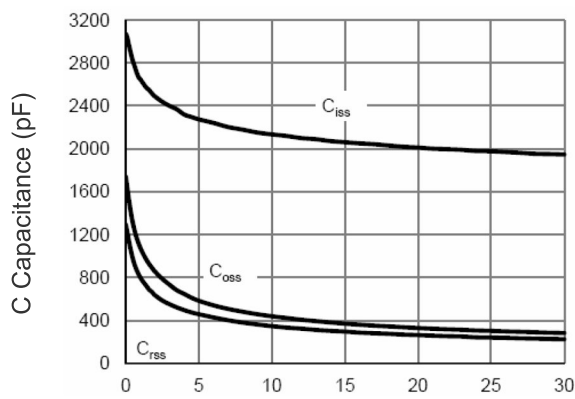

V_{DS} Drain-Source Voltage (V)

Figure 10 Capacitance vs Vds

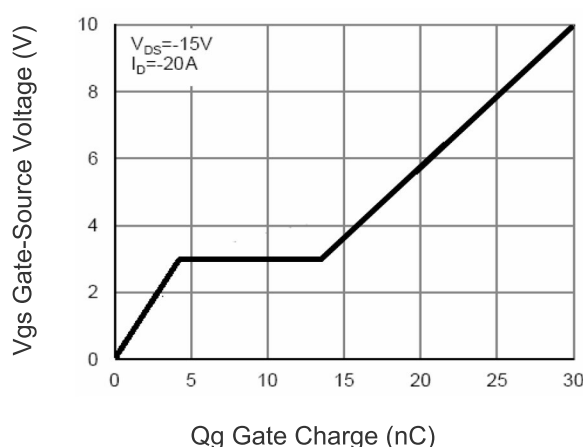

Q_g Gate Charge (nC)

Figure 11 Gate Charge

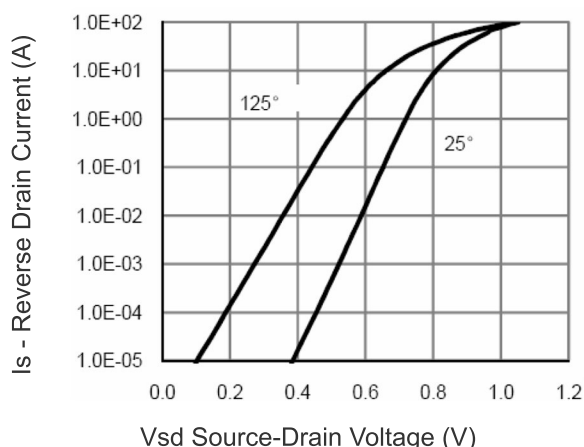

V_{SD} Source-Drain Voltage (V)

Figure 12 Source- Drain Diode Forward

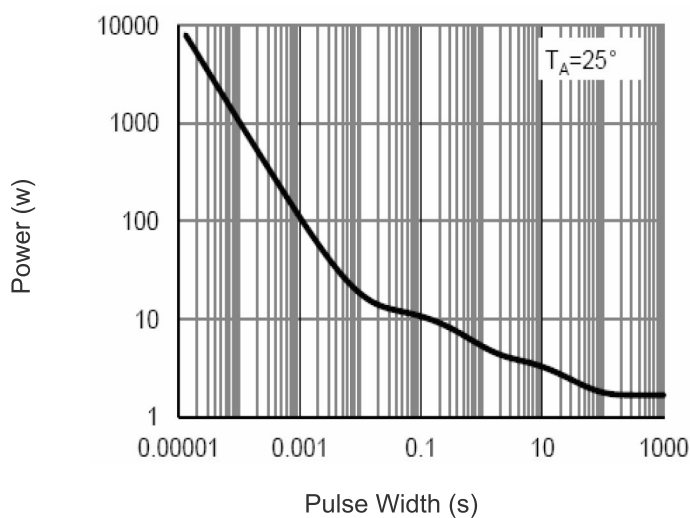


Figure 13 Single Pulse Power Rating Junction-to Ambient^(Note 6)

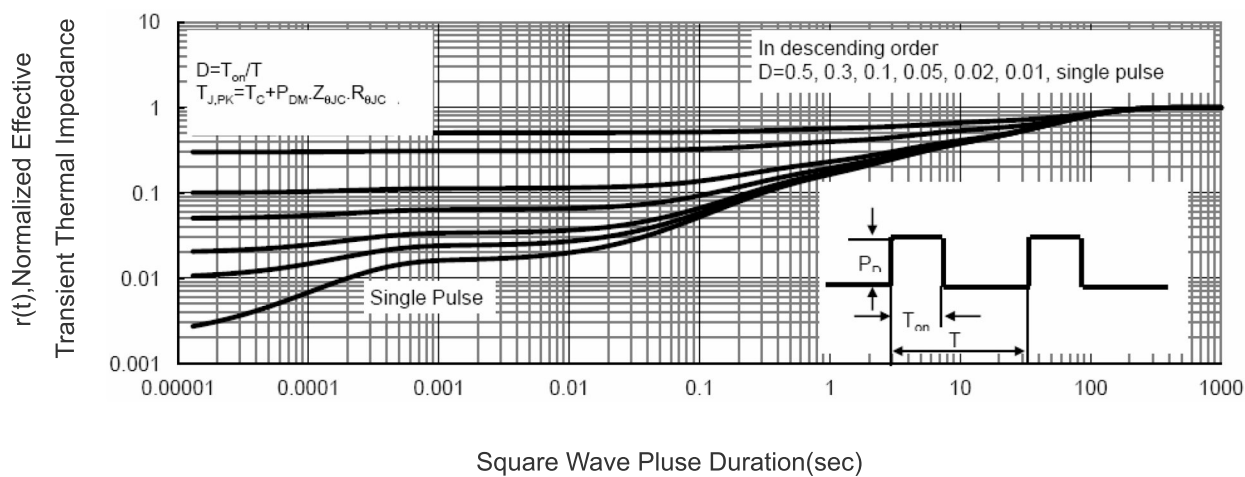
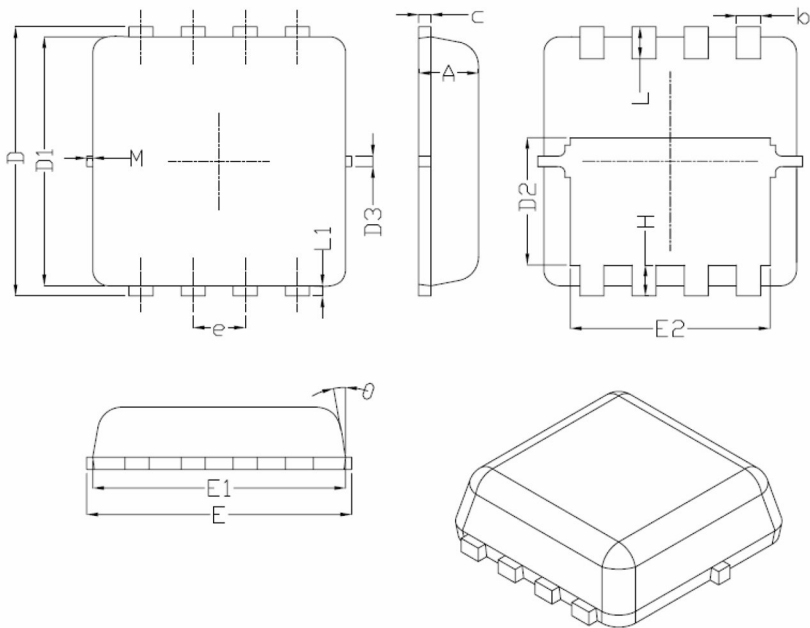


Figure 14 Normalized Maximum Transient Thermal Impedance

DFN3.3X3.3-8L Package Information



| Symbol | Dimensions In Millimeters | | |
|--------|---------------------------|------|------|
| | Min. | Nom. | Max. |
| A | 0.70 | 0.75 | 0.80 |
| b | 0.25 | 0.30 | 0.35 |
| c | 0.10 | 0.15 | 0.25 |
| D | 3.25 | 3.35 | 3.45 |
| D1 | 3.00 | 3.10 | 3.20 |
| D2 | 1.48 | 1.58 | 1.68 |
| D3 | - | 0.13 | - |
| E | 3.20 | 3.30 | 3.40 |
| E1 | 3.00 | 3.15 | 3.20 |
| E2 | 2.39 | 2.49 | 2.59 |
| e | 0.65BSC | | |
| H | 0.30 | 0.39 | 0.50 |
| L | 0.30 | 0.40 | 0.50 |
| L1 | - | 0.13 | - |
| M | * | * | 0.15 |
| θ | | 10° | 12° |

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